



**ZXTN19100CZ** 

#### **100V NPN MEDIUM POWER TRANSISTOR IN SOT89**

#### Features

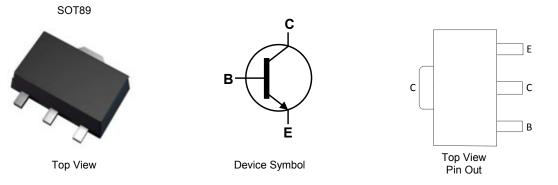
- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 5.25A High Continuous Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 65mV @ 1A</li>
- R<sub>sat</sub> = 44mΩ for a Low Equivalent On-Resistance
- Complementary part number: ZXTP19100CZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

#### Application

- PSU start up switch
- Motor drive
- Lamp, relay and solenoid switches

#### **Mechanical Data**

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.05 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTN19100CZTA	Standard	1L9	7	12	1,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### Marking Information



1L9 = Product Type Marking Code



#### Absolute Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
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Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage (forward blocking)	V <sub>CEX</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Collector voltage (reverse blocking)	V <sub>ECX</sub>	6	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current (Note 5)	lc	5.25	A
Base current	IB	1	A
Peak Pulse Collector Current (Single pulse)	ICM	10	A

#### Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	<b>D</b>	1.1	W
Linear Derating Factor	PD	8.8	mW/°C
Power Dissipation (Note 6)	D-	1.8	W
Linear Derating Factor	PD	14.4	mW/°C
Power Dissipation (Note 7)	P	2.4	W
Linear Derating Factor	PD	19.2	mW/°C
Power Dissipation (Note 8)	P	4.46	W
Linear Derating Factor	PD	35.7	mW/°C
Power Dissipation (Note 9)	D-	26.6	W
Linear Derating Factor	PD	213	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	117	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	68	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>0JA</sub>	51	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R <sub>0JA</sub>	28	°C/W
Thermal Resistance, Junction to Case (Note 9)	R <sub>eJC</sub>	4.69	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	С°

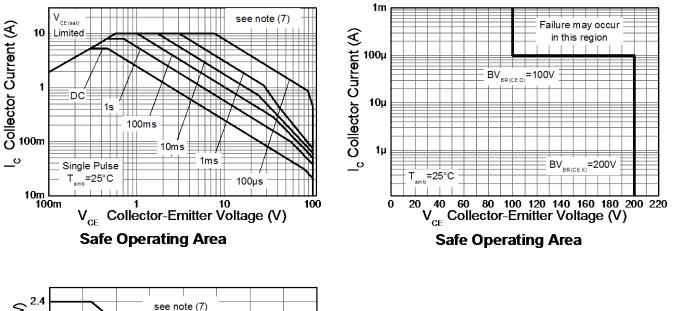
5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device Notes: measured when operating in steady state condition.

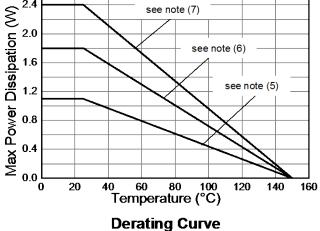
6. Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.
7. Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.
8. Same as note (5), the device is measured at t<5 seconds.</li>

9. Junction to case (collector tab). Typical.



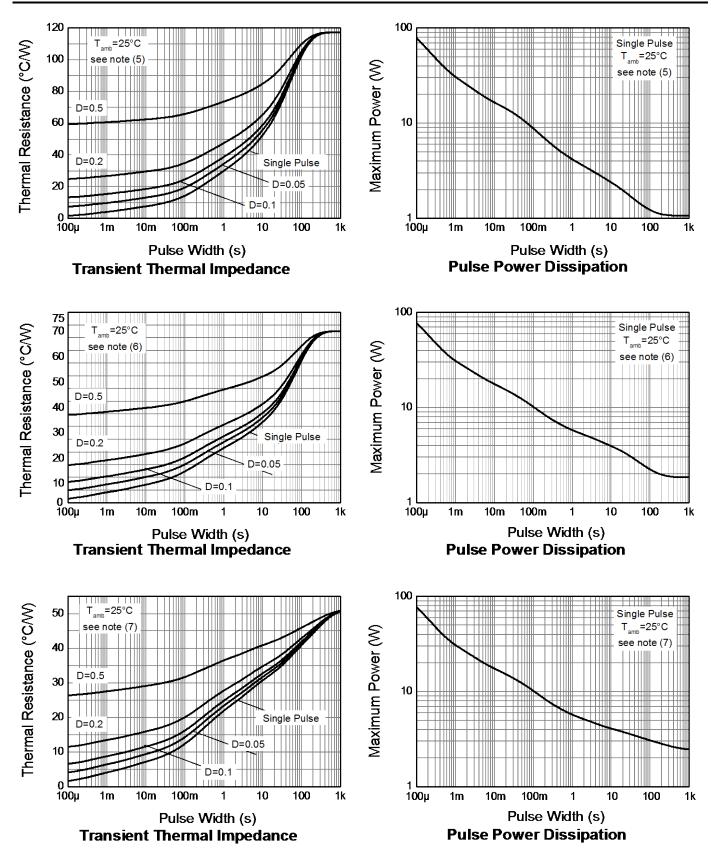
### **Thermal Characteristics and Derating Information**







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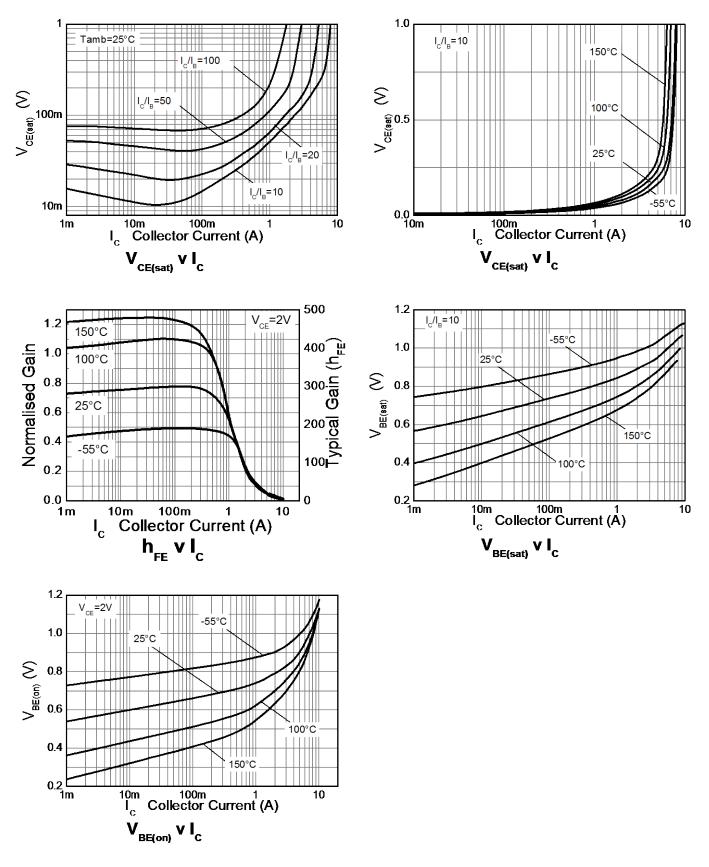
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	240	_	V	I <sub>C</sub> = 100μA
Collector-Emitter breakdown voltage (forward blocking)	BV <sub>CEX</sub>	200	240	_	V	$\label{eq:IC} \begin{split} I_C = 100 \mu A,  R_{BE} \leqslant 1 k \Omega \text{ or} \\ -1V < V_{BE} < 0.25 V \end{split}$
Collector- Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	120	_	V	I <sub>C</sub> = 10mA
Emitter-Collector breakdown voltage (reverse blocking)	BV <sub>ECX</sub>	6	8.3	—	V	$I_{E}$ = 100µA, $R_{BC} \le 1k\Omega$ or 0.25V > V <sub>BC</sub> > -0.25V
Emitter-Collector breakdown voltage (reverse blocking)	BV <sub>ECO</sub>	5	8	_	V	I <sub>E</sub> = 100μA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	_	V	I <sub>E</sub> = 100μA
Collector Base Cutoff Current	I <sub>CBO</sub>	—	1	50 0.5	nA μA	V <sub>CB</sub> = 200V V <sub>CB</sub> = 200V, T <sub>A</sub> = +100°C
Collector Emitter Cutoff Current	ICEX	_	_	100	nA	$V_{CE}$ = 200V, $R_{BE} \leqslant$ 1k $\Omega$ or -1V < $V_{BE}$ < 0.25V
Emitter Cutoff Current	I <sub>EBO</sub>	—	1	50	nA	V <sub>EB</sub> = 5.6V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	_	50 105 210	65 140 350	mV	$I_{C} = 1A, I_{B} = 100mA$ $I_{C} = 1A, I_{B} = 20mA$ $I_{C} = 5.25A, I_{B} = 525mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>		1000	1075	mV	I <sub>C</sub> = 5.25A, I <sub>B</sub> = 525mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	_	930	1025	mV	I <sub>C</sub> = 5.25A, V <sub>CE</sub> = 2V
DC current gain (Note 10)	h <sub>FE</sub>	200 130 —	300 200 30	500 — —	_	$I_{C} = 100mA, V_{CE} = 2V$ $I_{C} = 1A, V_{CE} = 2V$ $I_{C} = 5.25A, V_{CE} = 2V$
Transitional frequency	fT	_	150	_	MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V, f = 100MHz
Input Capacitance	Ci <sub>bo</sub>	_	305	400	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance	C <sub>obo</sub>	—	15.7	25	pF	V <sub>CB</sub> = 10V, f = 1MHz
Delay time	t <sub>d</sub>	—	28.3	—	ns	
Rise time	tr		23.6	—	ns	I <sub>C</sub> = 500mA, V <sub>CC</sub> = 10V,
Storage time	ts	_	962	—	ns	I <sub>B1</sub> = -I <sub>B2</sub> = 50mA
Fall time	t <sub>f</sub>		133	_	ns	

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



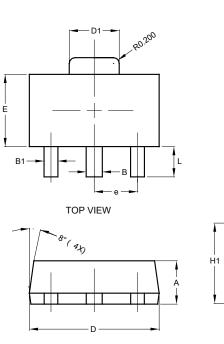
## Typical Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

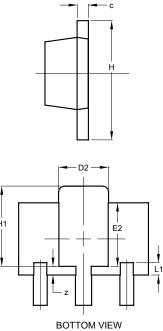




## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





SOT89

SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
z	0.20	0.40	0.30			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89
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Dimensions	Value (in mm)
С	1.500
G	0.244
Х	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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